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- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages

1CLR [14**[**] V_{CC} 1D [2 13 2CLR 1CLK 🛮 з 12 **[**] 2D 1PRE **[**] 4 11 1 2CLK 1റ ∏ 5 10 1 2 PRF 1**Q ∏** 6 9**∏** 2Q 8 D 2Q GND [

D, DGV, OR PW PACKAGE (TOP VIEW)

description

This dual positive-edge-triggered D-type flip-flop is designed for 1.65-V to 3.6-V V_{CC} operation.

A low level at the preset (\overline{PRE}) or clear (\overline{CLR}) inputs sets or resets the outputs, regardless of the levels of the other inputs. When \overline{PRE} and \overline{CLR} are inactive (high), data at the data (D) input meeting the setup time requirements is transferred to the outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the D input may be changed without affecting the levels at the outputs.

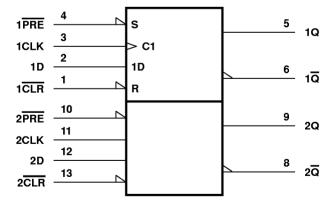
The SN74ALVC74 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

	INP	OUT	PUTS		
PRE	CLR	CLK	D	Q	Ø
L	Н	Х	Х	Н	٦
Н	L	Х	Χ	L	Н
L	L	Х	Χ	н†	н†
Н	Н	\uparrow	Н	Н	L
Н	Н	\uparrow	L	L	Н
Н	Н	L	Х	Q ₀	\overline{Q}_0

[†] This configuration is unstable; that is, it does not persist when PRE or CLR returns to its inactive (high) level.

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



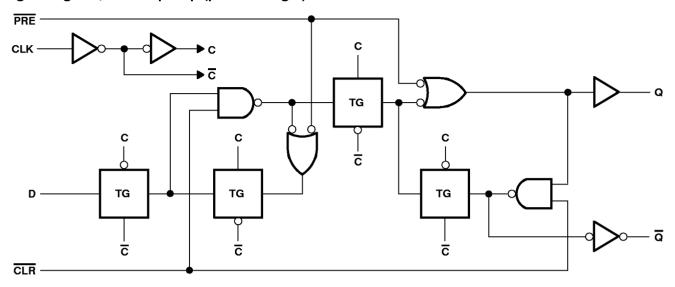
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logic diagram, each flip-flop (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Output voltage range, VO (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Input clamp current, $I_{ K }(V_{ } < 0)$	
Output clamp current, I _{OK} (V _O < 0)	
Continuous output current, IO	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): D package	127°C/W
DGV package	182°C/W
PW package	170°C/W
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. This value is limited to 4.6 V maximum.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.



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recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
V _{CC}	Supply voltage		1.65	3.6	٧	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}			
v_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2			
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$		
v_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		8.0		
VI	Input voltage		0	VCC	V	
٧o	Output voltage		0	Vcc	٧	
		V _{CC} = 1.65 V		-4		
la	High-level output current	$V_{CC} = 2.3 \text{ V}$		-12	mA	
ЮН		$V_{CC} = 2.7 \text{ V}$		-12		
		$V_{CC} = 3 V$		-24		
		V _{CC} = 1.65 V		4		
lOL	Low-level output current	V _{CC} = 2.3 V		12		
		V _{CC} = 2.7 V		12	mA	
	V _{CC} = 3 V			24		
Δt/Δν	Input transition rise or fall rate	-		10	ns/V	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	vcc	MIN	TYP† MAX	UNIT
	I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2	2	
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2		
	$I_{OH} = -6 \text{ mA}$	2.3 V	2		
Voн		2.3 V	1.7		V
	$I_{OH} = -12 \text{ mA}$	2.7 V	2.2		
		3 V	2.4		
	I _{OH} = −24 mA	3 V	2		
	I _{OL} = 100 μA	1.65 V to 3.6 V		0.2	
	$I_{OL} = 4 \text{ mA}$	1.65 V		0.45	
V	I _{OL} = 6 mA	2.3 V		0.4] ,
V _{OL}	10-40-4	2.3 V		0.7	·
	$I_{OL} = 12 \text{ mA}$	2.7 V		0.4	
	$I_{OL} = 24 \text{ mA}$	3 V		0.55	
lj	V _I = V _{CC} or GND	3.6 V		±5	μΑ
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V		20	μΑ
Δlcc	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V		750	μΑ
Ci	V _I = V _{CC} or GND	3.3 V			pF

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



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timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

			V _{CC} =	1.8 V	V _{CC} =	2.5 V 2 V	V _{CC} =	2.7 V	V _{CC} =	3.3 V 3 V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency										MHz
A Dulas dunation	Pulse duration	PRE or CLR low									ns
t _w	ruise duration	CLK high or low									115
	Oak and time a	Data before CLK↑									
^t su	Setup time	PRE or CLR inactive									ns
th	Hold time	Data after CLK↑									ns

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V	V _{CC} = 2.5 V ± 0.2 V	VC	c = 2.7 V	V _{CC} =	3.3 V 3 V	UNIT
	(IIVFO1)	(001701)	TYP	MIN MAX	МІ	N MAX	MIN	MAX	
f _{max}									MHz
+ .	CLK	Q or Q							ns
^t pd	PRE or CLR	Q or Q							115

operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		DARAMETER	TEST C	ONDITIONS	V _{CC} = 1.8V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT
ı	FARAWETER		12310	ONDITIONS	TYP	TYP	TYP	
ı	C _{pd}	Power dissipation capacitance per flip-flop	C _L = 0,	f = 10 MHz				pF



V_CC

0 V

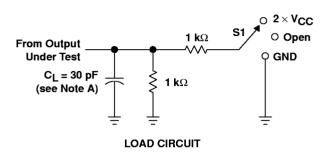
V_{CC}/2

SN74ALVC74 DUAL POSITIVE-EDGE-TRIGGERED D-TYPE FLIP-FLOP WITH CLEAR AND PRESET

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PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.8 V

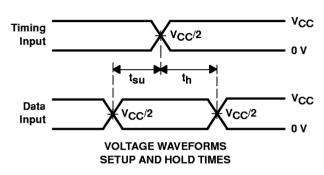
Input

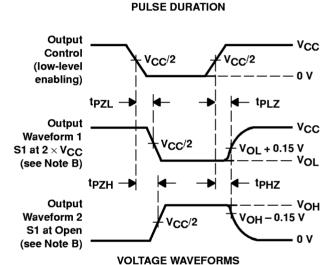


TEST	S1
tpd	Open
t _{PLZ} /t _{PZL}	2×V _{CC}
tPHZ/tPZH	GND

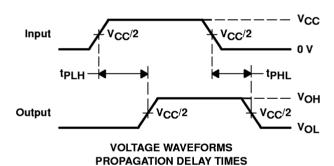
V_{CC}/2

VOLTAGE WAVEFORMS





ENABLE AND DISABLE TIMES



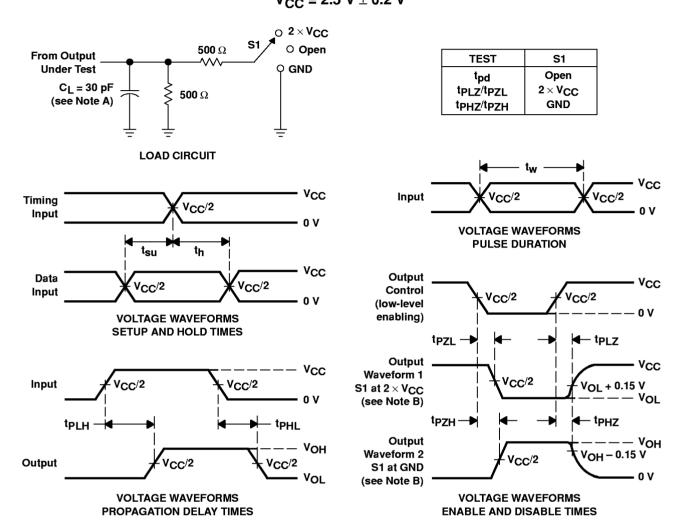
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as t_{dis}.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 V \pm 0.2 V$



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r \leq$ 2 ns, $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

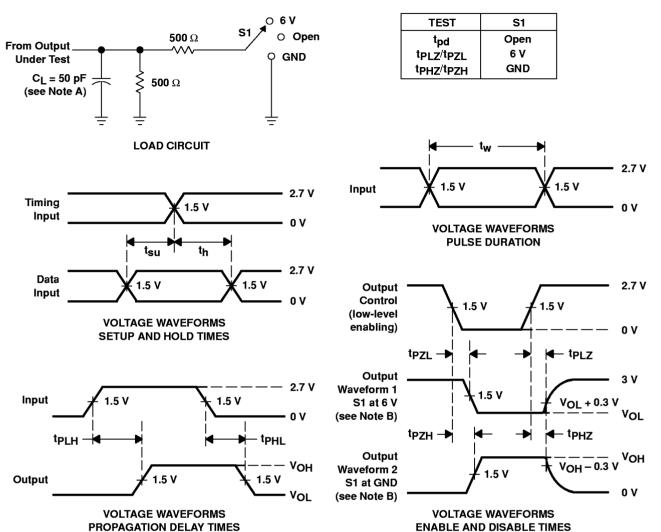
Figure 2. Load Circuit and Voltage Waveforms



PRODUCT PREVIEW

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PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns. $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tplz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten-
- G. tplH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms

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